



الجامعة الإسلامية العالمية ماليزيا

**INTERNATIONAL ISLAMIC UNIVERSITY MALAYSIA
END OF SEMESTER EXAMINATION
SEMESTER I, 2013/2014 SESSION
KULLI YAH OF ENGINEERING**

Programme : ENGINEERING Level of Study : UG 2
Time : 2:30 pm-5:30 pm Date : 08/01/2014
Duration : 3 Hrs
Course Code : ECE 2133 Section(s) : 1-2
Course Title : **Electronic Circuits**

This Question Paper consists of **Six (6)** Printed Pages (Including cover and a blank page) with **Five (5)** Questions.

INSTRUCTION(S) TO CANDIDATES

DO NOT OPEN UNTIL YOU ARE ASKED TO DO SO

- A total mark of this examination is **100**.
- This examination is worth **50%** of the total assessment.
- Answer **ALL FIVE (5)** questions.
- Useful formula and necessary parameters are given in page 6.

**Any form of cheating or attempt to cheat is a serious offence
which may lead to dismissal.**

Q.1 [20 marks]

- (a) Consider the circuit shown in **Fig. 1(a)**, derive the expression (step by step) of the voltage transfer function $T(s) = \frac{v_o(s)}{v_i(s)}$ and find the time constant and the corner frequency. **(10 marks)**

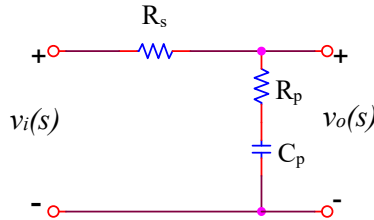


Fig. 1(a)

- (b) Draw the Bode plot (magnitude and phase) of the following transfer function. **(10 marks)**

$$H(s) = \frac{10^6(s+100)}{s}$$

Q.2 [20 marks]

- (a) The MOSFET circuit is shown in **Fig. 2(a)**, the transistor parameters are $g_m = 0.65 \text{ mA/V}$ and $r_o = 100 \text{ k}\Omega$. Draw the small signal equivalent circuit for the midband frequency range and find
- (i) the small signal voltage gain, $A_v = \frac{v_o}{v_i}$,
 - (ii) the lower corner frequency,
 - (iii) the equivalent output resistance R_o seen at the output terminals.

Given that $R_1 = 180 \text{ k}\Omega$, $R_2 = 330 \text{ k}\Omega$, $R_s = 1.0 \text{ k}\Omega$, $R_D = 10 \text{ k}\Omega$ and $C_C = 10 \mu\text{F}$.

(8 marks)

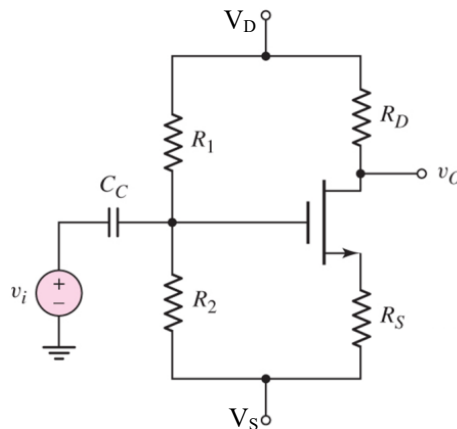


Fig. 2(a)

(b) The transistor circuit is shown in Fig. 2(b), the transistor has small-signal hybrid- π parameters, $r_\pi = 3 \text{ k}\Omega$, $g_m = 40\text{mA/V}$ and $r_o = \infty$. The circuit parameters are: $R_{Si} = 0.1 \text{ k}\Omega$, $R_1 = 60 \text{ k}\Omega$, $R_2 = 30 \text{ k}\Omega$, $R_E = 0.4 \text{ k}\Omega$, $R_C = 10 \text{ k}\Omega$, $R_L = 10 \text{ k}\Omega$, $C_C \rightarrow \infty$ and $C_L = 10 \text{ pF}$. Find the followings: **(12 marks)**

(iv) the small signal midband voltage gain, $A_v = \frac{v_o}{v_i}$,

(v) the midband current gain, $A_i = \frac{i_o}{i_i}$,

(vi) the higher corner frequency (3 dB frequency) due to C_L .

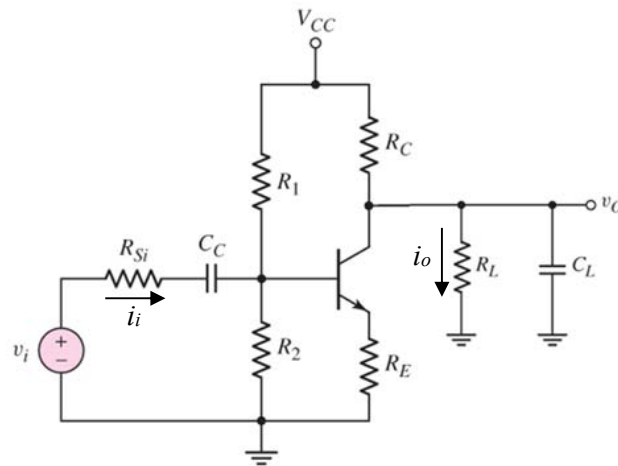


Fig. 2(b)

Q.3 [20 marks]

(a) Draw the simplified high frequency small-signal equivalent circuit diagram of the ac circuit shown in Fig. 3(a) and derive step by step short circuit current gain $A_i = \frac{I_c}{I_b}$. Then find the beta frequency f_β and cutoff frequency f_T and find the relation between gain and bandwidth. **(8 marks)**

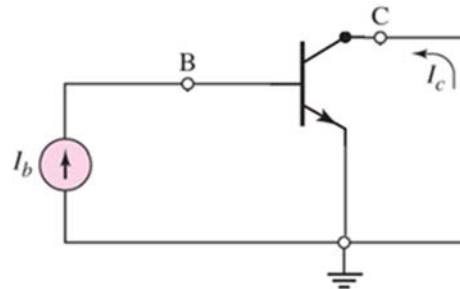


Fig. 3(a)

(b) The common emitter amplifier is shown in **Fig. 3(b)** and operated at high frequencies. The transistor parameters are: $r_{\pi} = 4 \text{ k}\Omega$, $g_m = 40 \text{ mA/V}$ and $r_o = \infty$, $C_{\pi} = 35 \text{ pF}$, and $C_{\mu} = 4 \text{ pF}$. **(12 marks)**

- (i) Draw the simplified high-frequency small signal equivalent circuit diagram.
- (ii) Find the Miller capacitance.
- (iii) Determine the upper 3dB frequency (f_H) considering Miller capacitance and without considering Miller capacitance.

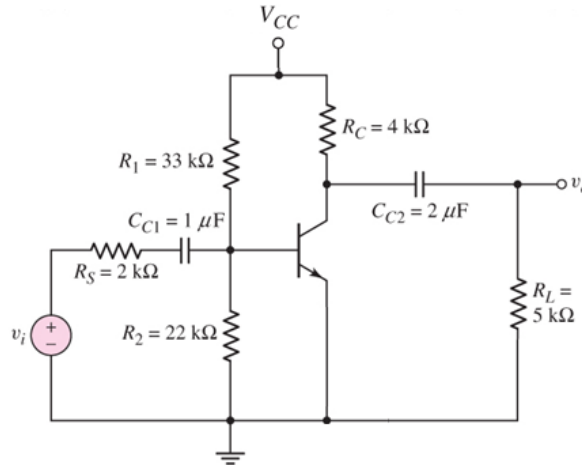


Fig. 3(b)

Q.4 [20 marks]

(a) The circuit diagram of a Wildar current source is shown in **Fig. 4(a)**. Design the circuit such that $I_o = 5\mu\text{A}$ and $I_{REF} = 50\mu\text{A}$ neglecting base current. Also determine V_{BE2} . [Given that $V^+ = 5 \text{ V}$, $V^- = -5 \text{ V}$, $V_{BE1} = 0.7 \text{ V}$ and $V_A = \infty$] **(10 marks)**

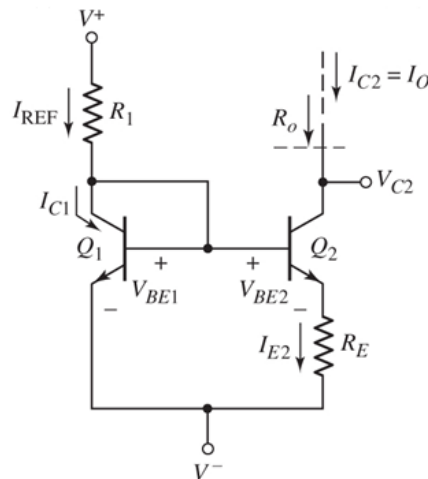


Fig. 4(a)

- (b) Design a MOSFET current source as shown in Fig. 4 (b) such that $I_{REF} = 0.5\text{mA}$ and $I_o = 1\text{mA}$, and $V_{DS(sat)} = 0.4\text{ V}$. The bias voltage $V^+ = +5\text{ V}$. The transistors are available with parameters $k'_n = 40\mu\text{A}/\text{V}^2$, $V_{TN} = 0.4\text{ V}$ and $\lambda = 0$. **(10 marks)**

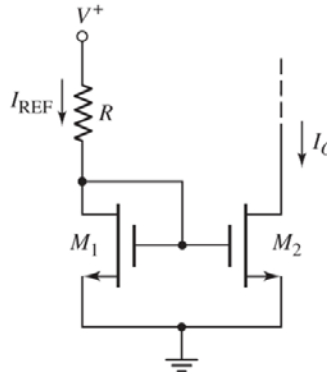


Fig. 4(b)

Q.5 [20 marks]

- (a) In a feedback amplifier, the open-loop low-frequency gain is $A_o = 10^6$ and the open-loop 3 dB frequency is 8 Hz. If the bandwidth of closed-loop system is 250 kHz, what is the maximum allowable value of the closed-loop low-frequency gain? **(5 marks)**
- (b) The ideal feedback amplifier topology is shown Fig. 5(b). Identify the type of feedback and derive step by step the closed loop current gain, A_{zf} , the input resistance, R_{if} and output resistance R_{of} . **(10 marks)**

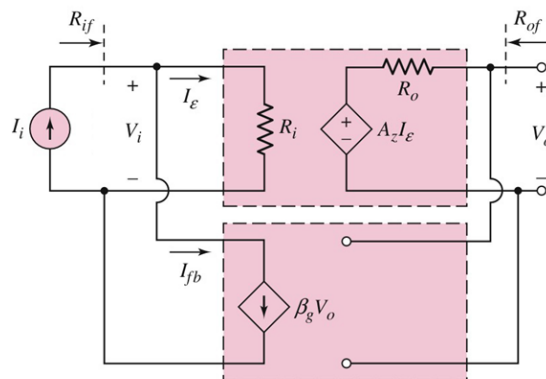


Fig. 5(b)

(b) The OP-amp feedback amplifier is shown Fig. 5(c). Identify the type of feedback and find the feedback factor, β . (5 marks)

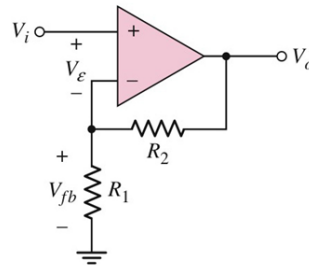


Fig. 5(c)

USEFUL FORMULA

BJT	MOSFET
$i_C = I_S e^{v_{BE}/V_T} \cdot \left(1 + \frac{v_{CE}}{V_A}\right)$ $g_m = \frac{I_{CQ}}{V_T}$ $r_\pi = \frac{\beta V_T}{I_{CQ}}$ $r_o = \frac{V_A}{I_{CQ}}$ $V_T = 26 \text{ mV}$ $V_{BE(on)} = 0.7 \text{ V}$	$I_D = \frac{1}{2} k'_n \left(\frac{W}{L}\right) (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$ $g_m = 2\sqrt{K_n I_{DQ}}$ $r_o = \frac{1}{\lambda I_{DQ}}$ $K_n = \frac{k'_n}{2} \left(\frac{W}{L}\right)$